

AMENDMENTS TO THE SPECIFICATION:

Please delete the title of the above-identified application in its entirety, and substitute therefor the following new title:

-- MANUFACTURING METHOD OF A SEMICONDUCTOR DEVICE HAVING ELECTRODES ON OPPOSED SIDES OF AN IC ELEMENT THEREOF AND FIRST AND SECOND CIRCUIT LAYERS ELECTRICALLY CONNECTED TO THE ELECTRODES --

Please delete the paragraph bridging pages 2 and 3 (that is, the paragraph beginning on page 2, line 6, to page 3, line 2), and substitute therefor the following new paragraph:

-- As shown in Fig. 1 (a), after IC elements 110 having a gold bump 114 formed on the circuit surface and in which all external electrodes are formed on the same face is separated into individual pieces by a dicing process, the individual pieces are sucked from a dicing film 100 using a vacuum suction unit 120. Next, as shown in Fig. 1 (b), the pieces are moved to a vacuum suction station 130 so that the gold bumps 114 of the IC elements 110 having all external electrodes formed on the same face thereof are made the upper face. Next, as shown in Fig. 1 (c) the vacuum suction station 130 is inverted such that the gold bumps 114 become the lower face. Next, the IC elements 110 having all of the external electrodes thereof formed on the same face are positioned in the determined position with respect to an antenna substrate 150, made by processing a polyimide base with copper film attached and manufacturing antenna circuits 151 on a base 152, and thereafter the IC elements 110 are secured in place by a thermal compression binding process using a heater ~~14040~~. Connections can then be formed at the connecting parts of the gold bumps

114 on the antenna circuit 151 by a tin-gold alloy formed by applying a tin or solder plating thereto. As shown in Fig. 1 (d), the gaps occurring between the IC elements 110 having all external electrodes formed on the same face thereof and the antenna substrate 150 are sealed using a thermoset resin ~~600~~ supplied from a dispenser 160. The condition of this thermoset resin once the hardening process is complete is the intermediate condition of the RFID tag called an inlet. Accommodating this inlet in a label or thin case enables it to be used as an RFID tag. --

Please delete the paragraph on page 4, lines 17-23, and substitute therefor the following new paragraph:

-- Further, if the available operating time is long then labor expenses increase concomitantly, mitigating against lower-cost manufacture, also as the connection between IC elements having all external electrodes formed on the same face thereof and an antenna substrate is realized using a gold-tin or gold solder connection, it is necessary to use as the substrate material, a taped substrate having copper film attached to polyimide~~polymide~~ film that is expensive but strongly resistant to heat. This makes it very difficult to manufacture the inlet economically. --

Please delete the paragraph on page 6, lines 20-23, and substitute therefor the following new paragraph:

-- It is preferable in this manufacturing method for the electronic device, that ~~the~~ after the step of positionally aligning the connection surfaces, there is a step of connecting at once, an electrode of the IC elements and at least one layer from among the first or the second circuit layers. --

Please delete the paragraph on page 7, lines 17-23, and substitute therefor the following new paragraph:

-- It is preferable in this manufacturing method for the electronic device that at least one of the first and second metallic films be supported on a base substrate comprised of an organic resin, and that this organic resin be selected from among polyvinyl chloride (PVC), acrylonitrile butadiene styrene (ABS), polyethylene terephthalate (PET), polyethylene terephthalate glycol (PETG), polyethylene naphthalate (PEN), polycarbonate resin (PC), biaxial polyester (O-PET), or polyimide~~polymide~~ resin. --

Please delete the paragraph on page 13, lines 9-14, and substitute therefor the following new paragraph:

-- In the first to third examples above, at least one of the first and second metallic films is supported on an organic resin or a base substrate comprised of paper. This organic resin may be selected from polyvinyl chloride (PVC), acrylonitrile butadiene styrene (ABS), polyethylene terephthalate (PET), polyethylene terephthalate glycol (PETG), polyethylene naphthalate (PEN), polycarbonate resin (PC), biaxial polyester (O-PET), or polyimide~~polymide~~ resin. --

Please delete the paragraph on page 17, lines 6-15, and substitute therefor the following new paragraph:

-- As the above described electric connection is made via an anisotropic conductive adhesive layer, in contrast to the case of the conventional art in which for example it is necessary when making a connection by a gold-tin alloy or the like to use a highly heat resistant polyimide~~polymide~~ as the base material for the first circuit

layer base substrate, it is possible to use cheaper polyethylene terephthalate. Further, as it is not necessary to use tin plating on the surface over the antenna circuit at the connecting part, it is possible to use cheaper aluminum that does not form well with a tin or solder coating as the material for the antenna circuit. Accordingly, a first circuit layer made by forming an aluminum antenna circuit on a polyethylene terephthalate base substrate is a satisfactory member for the manufacture of an inlet for a cheap RFID tag. --

Please delete the paragraph bridging pages 21 and 22 (that is, the paragraph beginning on page 21, line 15, to page 22, line 2), and substitute therefor the following new paragraph:

-- Next, as shown in Fig. 3 (e), once the IC element 10B inserted in the notch 74 of the disc shaped transport mechanism 73 is positioned over the anisotropic conductive adhesive layer 40, the IC element 10B is removed from the notch 74 by a temporary securing pin 75 and secured on the anisotropic conductive adhesive layer 40 and the second circuit layer 30 having the anisotropic conductive adhesive layer 40 is moved 3 mm. This operation is repeated over and over until 40 of the IC elements 10 are disposed on the anisotropic conductive adhesive layer 40 formed on the second circuit layer 30 at intervals of 3 mm. At this time, there are 24 of the notches 74 arranged circumferentially on the disc shaped transport mechanism 73, the disc shaped transport mechanism 73 rotates at a speed of 25 rotations per second and the second circuit ~~layer~~ layer 30 having the anisotropic conductive adhesive layer 40 moves at a speed of 18 mm per second. --